

and pressure of 0.1-30 gf/mm², and having a saturation moisture absorption of 1.0% by volume or less.

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cont

19. (Amended) A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-230°C temperature and pressure of 0.1-30 gf/mm², and having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

20. (Amended) A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-230°C temperature and pressure of 0.1-30 gf/mm², and having a void volume of 10% or less in terms of voids present in the material and at an interface between the material and a support member at a stage where a semiconductor has been bonded to a support member by the material.

21. (Amended) A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-230°C temperature and pressure of 0.1-30 gf/mm², having a residual volatile component in an amount of not more than 3.0% by weight.

22. (Amended) A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-230°C temperature and pressure of 0.1-30 gf/mm², having water absorption of 1.5% by volume or less.

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40. (Amended) A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminodiphenyl ether.

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43. (Amended) A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride), 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.
